Preferred Device

Small Signal MOSFET 150 mAmps, 60 Volts

N-Channel TO-92

Features

Pb–Free Packages are Available*



Rating	Symbol	Value	Unit
Drain – Source Voltage	V _{DSS}	60	Vdc
Drain–Gate Voltage (R _{GS} = 1.0 MΩ)	V_{DGR}	60	Vdc
Gate–Source Voltage – Continuous – Non–repetitive ($t_p \le 50 \mu s$)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current - Continuous - Pulsed	I _D I _{DM}	150 1000	mAdc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	400 3.2	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	TL	300	°C

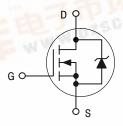


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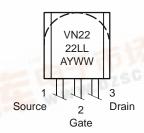
150 mA, 60 V $R_{DS(on)}$ = 7.5 Ω

N-Channel





MARKING DIAGRAM & PIN ASSIGNMENT



A = Assembly Location

Y = Year WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_C = 25^{\circ}C \ unless \ otherwise \ noted)$

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•		
Drain–Source Breakdown Voltage (V _{GS} = 0, I _D = 100 μAdc)		V _{(BR)DSS}	60	-	Vdc
Zero Gate Voltage Drain Current $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0)$ $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0, T_J = 125^{\circ}\text{C})$		I _{DSS}	_ _	10 500	μAdc
Gate-Body Leakage Current, Forward (V _{GSF} = 30 Vdc, V _{DS} = 0)		I _{GSSF}	_	-100	nAdc
ON CHARACTERISTICS (Note 1)					
Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.0 mAdc)		V _{GS(th)}	0.6	2.5	Vdc
Static Drain–Source On–Resistance $(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Vdc}, T_C = 125^{\circ}\text{C})$		r _{DS(on)}	- -	7.5 13.5	Ω
Drain–Source On–Voltage ($V_{GS} = 5.0 \text{ Vdc}$, $I_D = 200 \text{ mAdc}$) ($V_{GS} = 10 \text{ Vdc}$, $I_D = 500 \text{ mAdc}$)		V _{DS(on)}	- -	1.5 3.75	Vdc
On–State Drain Current $(V_{GS} = 10 \text{ Vdc}, V_{DS} \ge 2.0 \text{ V}_{DS(on)})$		I _{D(on)}	750	-	mA
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 500 mAdc)		9fs	100	-	μmhos
DYNAMIC CHARACTERISTICS		-	<u>-</u>	- <u>-</u>	-
Input Capacitance		C _{iss}	_	60	pF
Output Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0,$ f = 1.0 MHz)	Coss	_	25	
Reverse Transfer Capacitance]	C _{rss}	_	5.0	
SWITCHING CHARACTERISTICS (Note 1)					
Turn-On Delay Time	$(V_{DD} = 15 \text{ Vdc}, I_D = 600 \text{ mA},$	t _{on}	-	10	ns
Turn-Off Delay Time	$R_{gen} = 25 \Omega, R_L = 23 \Omega$	t _{off}	_	10	

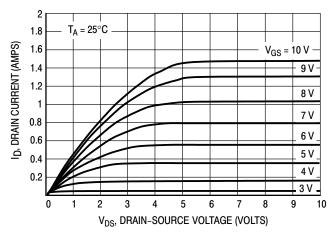
^{1.} Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

Device	Package	Shipping [†]
VN2222LL	TO-92	1000 Unit / Box
VN2222LLG	TO-92 (Pb-Free)	1000 Unit / Box
VN2222LLRL	TO-92	1000 Unit / Box
VN2222LLRLRA	TO-92	2000 Tape & Reel
VN2222LLRLRAG	TO-92 (Pb-Free)	2000 Tape & Reel
VN2222LLRLRM	TO-92	2000 Unit / Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

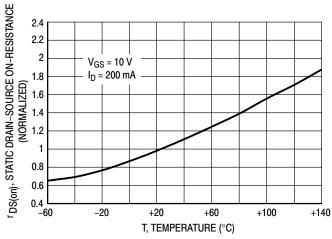
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0.8 V_{DS} = 10 V 25°C 125°C 12

Figure 1. Ohmic Region

Figure 2. Transfer Characteristics



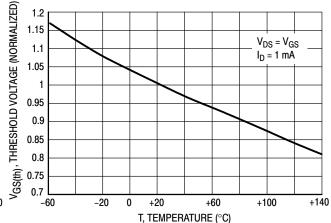
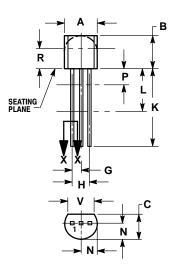


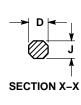
Figure 3. Temperature versus Static Drain–Source On–Resistance

Figure 4. Temperature versus Gate Threshold Voltage

PACKAGE DIMENSIONS

TO-92 CASE 29-11 **ISSUE AL**





- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		INCHES MILLIM		IETERS
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
V	0 135		3 43		

STYLE 22:

PIN 1. SOURCE

- 2. GATE
- 3. DRAIN

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